

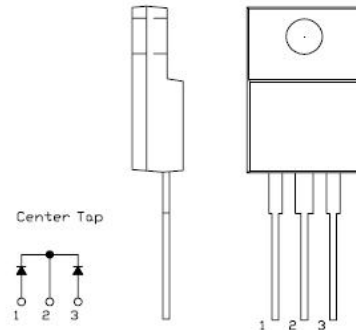
MURF1620CT ULTRAFAST RECTIFIER

Applications:

- Switching Power Supply
- Power Switching Circuits
- General Purpose

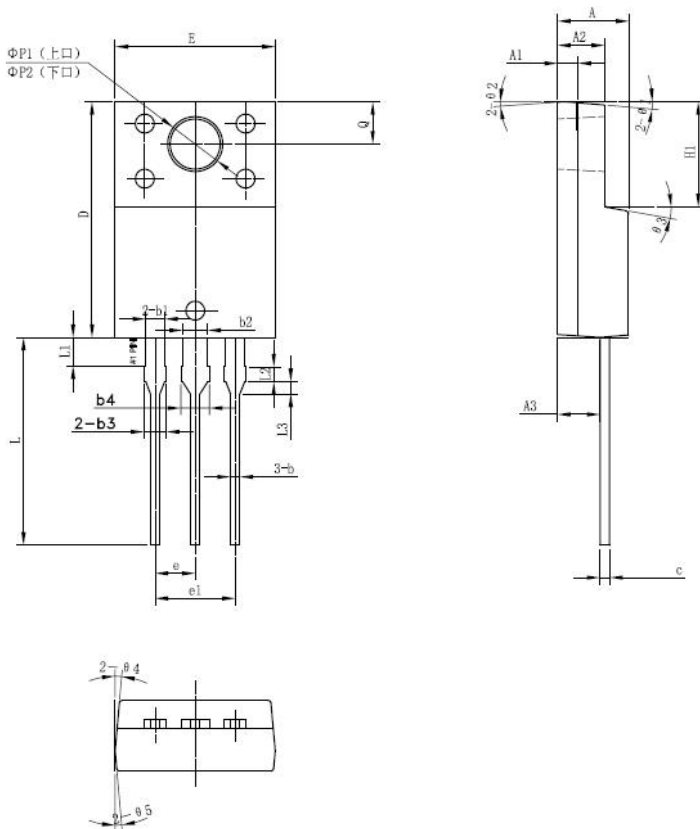
Features:

- Ultra-Fast Switching
- High Current Capability
- Low Reverse Leakage Current
- High Surge Current Capability
- Plastic Material has UL Flammability Classification 94V-0
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



OUTLINE DRAWING

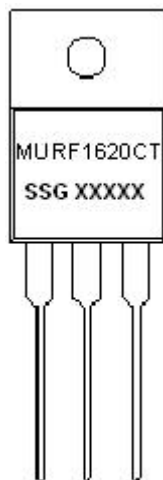
Mechanical Dimensions: In mm



SYMBOL	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
c	0.55	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦP1(上口)	3.30	3.50	3.70
ΦP2(下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

ITO-220AB

Marking Diagram:



Where XXXXX is YYWWL

MUR = Device Type
 F = Package type
 16 = Forward Current (16A)
 20 = Reverse Voltage (200V)
 CT = Configuration
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MURF1620CT	ITO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings and Electrical Characteristics @ $T_A=25^{\circ}\text{C}$ unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	MURF1620CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	200	V
Average Rectified Output Current @ $T_A = 55^{\circ}\text{C}$	I_o	16.0	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	125	A
Forward Voltage (per element) @ $I_F = 8.0\text{A}$, $T_J=25^{\circ}\text{C}$	V_{FM1}	1.5	V
Peak Reverse Current @ $T_A = 25^{\circ}\text{C}$ At Rated DC Blocking Voltage @ $T_A = 125^{\circ}\text{C}$	I_R	10 500	μA
Maximum Reverse Recovery Time (Note 1)	T_{rr}	35	ns
Typical Junction Capacitance (Note 2)	C_J	80	pF
Operating and Storage Temperature Range	T_J , T_{STG}	-55 to +150	$^{\circ}\text{C}$
Approximate Weight	wt	2.0	g
Case Style	ITO-220AB		

Note: 1.Measured with $I_F=0.5\text{A}$; $I_R=1.0\text{A}$; $I_{RR}=0.25\text{A}$.

2.Measured at 1.0MHz and applied reverse voltage of 4.0V D.C.

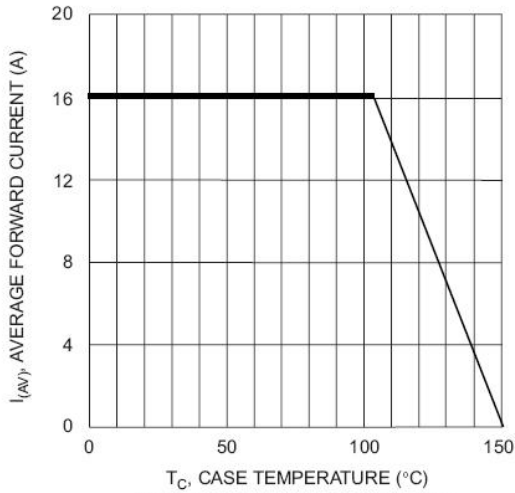


Fig. 1 Forward Current Derating Curve

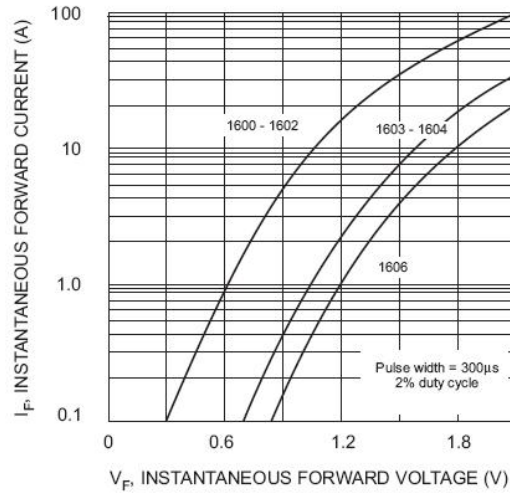


Fig. 2 Typical Forward Characteristics

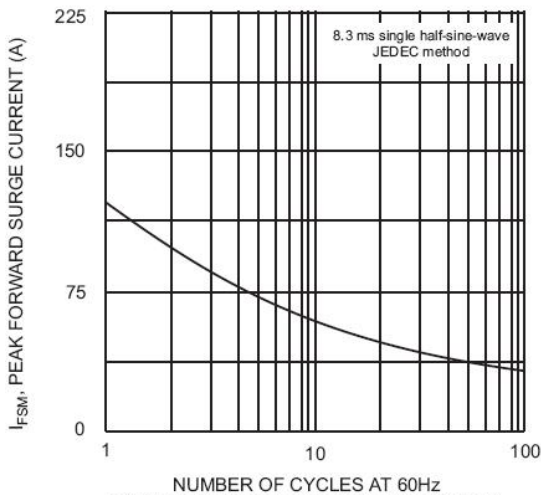


Fig. 3 Maximum Non-Repetitive Surge Current

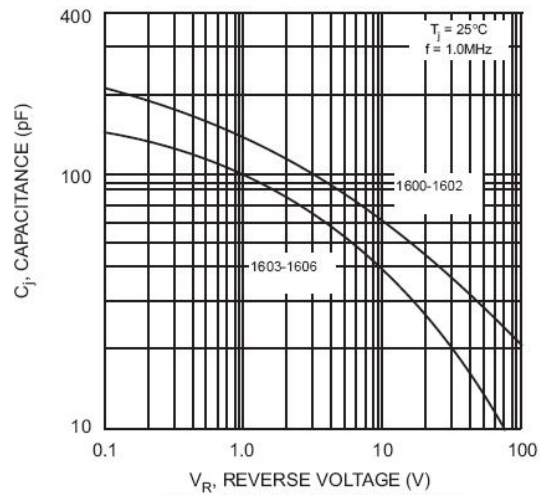
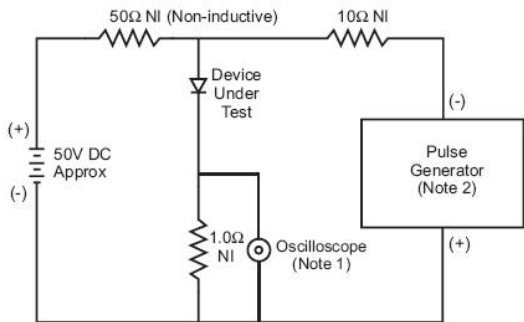


Fig. 4 Typical Junction Capacitance



Notes:
1. Rise Time = 7.0ns max. Input Impedance = 1.0M Ω , 22pF.
2. Rise Time = 10ns max. Input Impedance = 50 Ω .

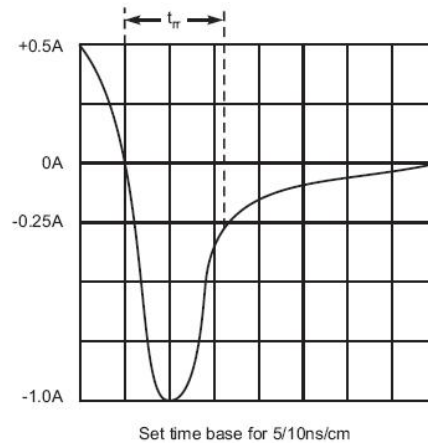


Fig. 5 Reverse Recovery Time Characteristic and Test Circuit

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